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Supplementary Data for

Effect of an ultrathin Fe interlayer on the growth of MnGa and spin-orbit-torque induced magnetization switching

§1 Experimental conditions of current-induced magnetization switching for a MnGa(2)/Fe(0.6) bilayer and a MnGa(2) single layer

After the magnetization direction was aligned by applying an out-of-plane magnetic field of $\mu_0 H_z = -0.5$ T or 0.5 T, a current pulse I_P with a duration of 100 µs was applied to the channel (+*x* direction) while varying the amplitude from -10 mA to 10 mA. For deterministic switching, an in-plane magnetic field $\mu_0 H_x = \pm 10$ mT was applied along the *x*-axis. R_{yx} was measured with a sensing current *I* of 100 µA after application of each I_P .



Fig. S1.Measurement configuration for SOT-induced switching.

§2 Measurement of effective magnetic field originating SOT acting on the magnetization of domain walls

Since the coercive field is much smaller than H_k in both MnGa/Fe bilayer and MnGa single layer [see Figs. 3(a), (b)], the DWs were introduced during the magnetization reversal. Following the method proposed by C. Pai et al. [31], we measured the modulation of coercive field by the Slonczewski-like SOT assisted DW motion. The effective magnetic field originating from the Slonczewski-like SOT is given by $H_{\text{eff}} \mathbf{m} \times \mathbf{y}$, where **m** is the unit vector along the magnetization, and **y** is the unit vector along the y-axis. Thus, when the *x*-component of magnetization is induced in the DWs by the application of H_x , an effective magnetic field along z-axis is exerted on magnetization in the DWs, and it induces a shift in the out-of-plane hysteresis loop by an amount H_{eff} . The measurements were carried out in a cryostat kept at 250 K to reduce effects of Joule heating arising from the applied DC current.

§3 Effect of Rashba and Dresselhaus spin orbit interactions at Fe/GaAs interface on SOT efficiency

Chen et al. observed a sizable spin-orbit field (SOF) originated from Rashba and Dresselhaus spin orbit interactions at the epitaxial Fe/GaAs interface [33]. The magnitude of SOF is maximized (minimized) when the current direction is along [110] ([1-10]). If such SOF is produced in the Fe/GaAs interface, the SOT-induced effective field should have certain current direction dependence. Figure S2 shows $\mu_0 H_{eff}$ as a function of $\mu_0 H_x$ for a MnGa/Fe bilayer. The black squares (red triangles) in the figure indicate $\mu_0 H_{eff}$ when the current and H_x directions are along [110] ([1-10]). No significant difference was observed, indicating that we have no direct evidence for the presence of such SOFs in our devices.



Fig. S2. $\mu_0 H_{\text{eff}}$ at I = 5 mA as a function of $\mu_0 H_x$ for a MnGa/Fe bilayer with different current direction.